

Nikolai B Smirnov

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

236
papers

3,955
citations

34
h-index

47
g-index

236
ext. papers

4,291
ext. citations

2.4
avg, IF

4.9
L-index

#	Paper	IF	Citations
236	1 GeV proton damage in Ga_2O_3 . <i>Journal of Applied Physics</i> , 2021 , 130, 185701	2.5	1
235	Experimental estimation of electron-hole pair creation energy in Ga_2O_3 . <i>Applied Physics Letters</i> , 2021 , 118, 202106	3.4	8
234	Crystal orientation dependence of deep level spectra in proton irradiated bulk Ga_2O_3 . <i>Journal of Applied Physics</i> , 2021 , 130, 035701	2.5	4
233	Photosensitivity of Ga_2O_3 Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. <i>APL Materials</i> , 2020 , 8, 111105	5.7	13
232	Anisotropy of hydrogen plasma effects in bulk n-type Ga_2O_3 . <i>Journal of Applied Physics</i> , 2020 , 127, 175702	2.5	14
231	Assessing mobile ions contributions to admittance spectra and current-voltage characteristics of 3D and 2D/3D perovskite solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2020 , 215, 110670	6.4	9
230	Pulsed fast reactor neutron irradiation effects in Si doped n-type Ga_2O_3 . <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 274001	3	13
229	Electric field dependence of major electron trap emission in bulk Ga_2O_3 : Poole-Frenkel effect versus phonon-assisted tunneling. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 304001	3	9
228	Editor's Choice: Electrical Properties and Deep Traps in Ga_2O_3 :Sn Films Grown on Sapphire by Halide Vapor Phase Epitaxy. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 045003	2	10
227	Ion Dynamics in Single and Multi-Cation Perovskite. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 065015	2	3
226	Role of hole trapping by deep acceptors in electron-beam-induced current measurements in Ga_2O_3 vertical rectifiers. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 495108	3	11
225	Effects of 5 MeV electron irradiation on deep traps and electroluminescence from near-UV InGaN/GaN single quantum well light-emitting diodes with and without InAlN superlattice underlayer. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 445111	3	3
224	Effects of InAlN underlayer on deep traps detected in near-UV InGaN/GaN single quantum well light-emitting diodes. <i>Journal of Applied Physics</i> , 2019 , 126, 125708	2.5	14
223	Electrical Properties, Deep Trap and Luminescence Spectra in Semi-Insulating, Czochralski Ga_2O_3 (Mg). <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3019-Q3023	2	25
222	Defects at the surface of Ga_2O_3 produced by Ar plasma exposure. <i>APL Materials</i> , 2019 , 7, 061102	5.7	25
221	Deep trap analysis in green light emitting diodes: Problems and solutions. <i>Journal of Applied Physics</i> , 2019 , 125, 215701	2.5	5
220	Deep trap spectra of Sn-doped Ga_2O_3 grown by halide vapor phase epitaxy on sapphire. <i>APL Materials</i> , 2019 , 7, 051103	5.7	22

219	Electrical Properties, Deep Levels and Luminescence Related to Fe in Bulk Semi-Insulating EgGa_2O_3 Doped with Fe. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3091-Q3096	2	19
218	Deep traps and persistent photocapacitance in $\text{E}(\text{Al}_{0.14}\text{Ga}_{0.86})_2\text{O}_3/\text{Ga}_2\text{O}_3$ heterojunctions. <i>Journal of Applied Physics</i> , 2019 , 125, 095702	2.5	1
217	Hydrogen plasma treatment of EgGa_2O_3 : Changes in electrical properties and deep trap spectra. <i>Applied Physics Letters</i> , 2019 , 115, 032101	3.4	29
216	Effects of Hydrogen Plasma Treatment Condition on Electrical Properties of EgGa_2O_3 . <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P661-P666	2	4
215	Defect States Determining Dynamic Trapping-Detrapping in EgGa_2O_3 Field-Effect Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3013-Q3018	2	19
214	Trapping Phenomena in InAlN/GaN High Electron Mobility Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q1-Q7	2	9
213	Point defect induced degradation of electrical properties of Ga_2O_3 by 10 MeV proton damage. <i>Applied Physics Letters</i> , 2018 , 112, 032107	3.4	72
212	Compensation and persistent photocapacitance in homoepitaxial Sn-doped EgGa_2O_3 . <i>Journal of Applied Physics</i> , 2018 , 123, 115702	2.5	57
211	Electrical Properties of Bulk, Non-Polar, Semi-Insulating M-GaN Grown by the Ammonothermal Method. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P260-P265	2	11
210	Quantum Barrier Growth Temperature Affects Deep Traps Spectra of InGaN Blue Light Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q80-Q84	2	7
209	Diffusion length of non-equilibrium minority charge carriers in EgGa_2O_3 measured by electron beam induced current. <i>Journal of Applied Physics</i> , 2018 , 123, 185704	2.5	37
208	Defect States Induced in GaN-Based Green Light Emitting Diodes by Electron Irradiation. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P323-P328	2	9
207	Trap states in multication mesoscopic perovskite solar cells: A deep levels transient spectroscopy investigation. <i>Applied Physics Letters</i> , 2018 , 113, 263501	3.4	24
206	Electrical properties, structural properties, and deep trap spectra of thin EgGa_2O_3 films grown by halide vapor phase epitaxy on basal plane sapphire substrates. <i>APL Materials</i> , 2018 , 6, 121110	5.7	26
205	Electrical properties of bulk semi-insulating EgGa_2O_3 (Fe). <i>Applied Physics Letters</i> , 2018 , 113, 142102	3.4	59
204	Hole traps and persistent photocapacitance in proton irradiated EgGa_2O_3 films doped with Si. <i>APL Materials</i> , 2018 , 6, 096102	5.7	50
203	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated EgGa_2O_3 . <i>Applied Physics Letters</i> , 2018 , 113, 092102	3.4	46
202	Current relaxation analysis in AlGaN/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017 , 35, 011207	1.3	7

201	Effect of nanopillar sublayer embedded with SiO ₂ on deep traps in green GaN/InGaN light emitting diodes. <i>Journal of Applied Physics</i> , 2017 , 121, 045108	2.5	9
200	Changes in electron and hole traps in GaN-based light emitting diodes from near-UV to green spectral ranges. <i>Applied Physics Letters</i> , 2017 , 110, 192107	3.4	16
199	Defects responsible for lifetime degradation in electron irradiated n-GaN grown by hydride vapor phase epitaxy. <i>Applied Physics Letters</i> , 2017 , 110, 112102	3.4	21
198	Deep Electron and Hole Traps in Electron-Irradiated Green GaN/InGaN Light Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, Q127-Q131	2	9
197	Gate-Lag in AlGa _N /Ga _N High Electron Mobility Transistors: A Model of Charge Capture. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, S3034-S3039	2	10
196	Degradation-induced low frequency noise and deep traps in GaN/InGaN near-UV LEDs. <i>Applied Physics Letters</i> , 2017 , 111, 062103	3.4	13
195	Point defects controlling non-radiative recombination in GaN blue light emitting diodes: Insights from radiation damage experiments. <i>Journal of Applied Physics</i> , 2017 , 122, 115704	2.5	19
194	Electron irradiation of near-UV GaN/InGaN light emitting diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1700372	1.6	10
193	Deep Electron Traps Responsible for Higher Quantum Efficiency in Improved GaN/InGaN Light Emitting Diodes Embedded with SiO ₂ Nanoparticles. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, Q274-Q277	2	13
192	Deep traps determining the non-radiative lifetime and defect band yellow luminescence in n-GaN. <i>Journal of Alloys and Compounds</i> , 2016 , 686, 1044-1052	5.7	24
191	Electrical, luminescent, and deep trap properties of Si doped n-GaN grown by pendeo epitaxy. <i>Journal of Applied Physics</i> , 2016 , 119, 015103	2.5	23
190	Studies of deep level centers determining the diffusion length in epitaxial layers and crystals of undoped n-GaN. <i>Journal of Applied Physics</i> , 2016 , 119, 205109	2.5	23
189	Deep traps and instabilities in AlGa _N /Ga _N high electron mobility transistors on Si substrates. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 041216	1.3	13
188	Electrical, Luminescent and Structural Properties of Nanopillar GaN/InGaN Multi-Quantum-Well Structures Prepared by Dry Etching. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, Q165-Q170		8
187	Deep Traps in AlGa _N /Ga _N High Electron Mobility Transistors on SiC. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, Q260-Q265	2	8
186	Electron traps as major recombination centers in n-GaN films grown by metalorganic chemical vapor deposition. <i>Applied Physics Express</i> , 2016 , 9, 061002	2.4	13
185	Improved GaN films with low background doping and low deep trap density grown by hydride vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 341-344		
184	Deep level transient spectroscopy in III-Nitrides: Decreasing the effects of series resistance. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 061203	1.3	41

183	Photoluminescence enhancement by localized surface plasmons in AlGa _N /Ga _N /AlGa _N double heterostructures. <i>Physica Status Solidi - Rapid Research Letters</i> , 2015 , 9, 575-579	2.5	4
182	Recombination and trapping centers in pure and doped TlBr crystals. <i>Semiconductors</i> , 2014 , 48, 1123-1133	3.7	
181	Electrical, optical, and structural properties of GaN films prepared by hydride vapor phase epitaxy. <i>Journal of Alloys and Compounds</i> , 2014 , 617, 200-206	5.7	10
180	Spatial location of the Ec-0.6 eV electron trap in AlGa _N /Ga _N heterojunctions. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 050602	1.3	18
179	Hydride vapor phase GaN films with reduced density of residual electrons and deep traps. <i>Journal of Applied Physics</i> , 2014 , 115, 183706	2.5	11
178	Electrical Characteristics and Deep Traps Spectra of Undoped GaN Films Grown on Si Using Different Strain-Relieving Buffer Types. <i>IEEE Nanotechnology Magazine</i> , 2014 , 13, 151-159	2.6	2
177	Electrical and structural properties of GaN films and GaN/InGa _N light-emitting diodes grown on porous GaN templates fabricated by combined electrochemical and photoelectrochemical etching. <i>Journal of Alloys and Compounds</i> , 2014 , 589, 507-512	5.7	18
176	DEEP TRAPS SPECTRA IN UNDOPED GAN FILMS GROWN BY HYDRIDE VAPOR PHASE EPITAXY UNDER VARIOUS CONDITIONS. <i>American Journal of Applied Sciences</i> , 2014 , 11, 1714-1721	0.8	1
175	Deep hole traps in undoped n-GaN films grown by hydride vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2014 , 115, 223702	2.5	34
174	Structural defects responsible for excessive leakage current in Schottky diodes prepared on undoped n-GaN films grown by hydride vapor phase epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 051212	1.3	4
173	Properties of nanopillar structures prepared by dry etching of undoped GaN grown by maskless epitaxial overgrowth. <i>Journal of Alloys and Compounds</i> , 2013 , 554, 258-263	5.7	9
172	Effects of annealing in oxygen on electrical properties of AlGa _N /Ga _N heterostructures grown on Si. <i>Journal of Alloys and Compounds</i> , 2013 , 575, 17-23	5.7	9
171	Temperature stability of high-resistivity GaN buffer layers grown by metalorganic chemical vapor deposition. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 051208	1.3	13
170	Electrical properties of undoped GaN films grown by maskless epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 2013 , 113, 083712	2.5	12
169	Effect of electron irradiation on AlGa _N /Ga _N and InAlN/GaN heterojunctions. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 022206	1.3	19
168	Deep centers and persistent photocapacitance in AlGa _N /Ga _N high electron mobility transistor structures grown on Si substrates. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 011211	1.3	14
167	Electronic properties and deep traps in electron-irradiated n-GaN. <i>Semiconductors</i> , 2012 , 46, 433-439	0.7	5
166	Effect of buffer layer structure on electrical and structural properties of AlGa _N /Ga _N high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 011205	1.3	13

165	Comparison of neutron irradiation effects in AlGaN/AlN/GaN, AlGaN/GaN, and InAlN/GaN heterojunctions. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012 , 30, 061207	1.3	28
164	Deep traps and enhanced photoluminescence efficiency in nonpolar a-GaN/InGaN quantum well structures. <i>Journal of Applied Physics</i> , 2012 , 111, 033103	2.5	4
163	Electrical properties and radiation detector performance of free-standing bulk n-GaN. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012 , 30, 021205	1.3	26
162	Admittance Spectra Studies of Quantum Well States in AlGaN/AlN/GaN Heterojunctions. <i>ECS Journal of Solid State Science and Technology</i> , 2012 , 1, P152-P156	2	5
161	Metastable centers in AlGaN/AlN/GaN heterostructures. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012 , 30, 041209	1.3	12
160	Electrical and luminescent properties and deep traps spectra in GaN nanopillar layers prepared by dry etching. <i>Journal of Applied Physics</i> , 2012 , 112, 073112	2.5	14
159	Characteristics of a-GaN films and a-AlGaN/GaN heterojunctions prepared on r-sapphire by two-stage growth process. <i>Journal of Applied Physics</i> , 2011 , 110, 093709	2.5	8
158	Structural and electric properties of AlN substrates used for LED Heterostructures growth. <i>Russian Microelectronics</i> , 2011 , 40, 629-633	0.5	1
157	Deep traps and thermal measurements on AlGaN/GaN on Si transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2011 , 29, 042201	1.3	5
156	Deep electron and hole traps in neutron transmutation doped n-GaN. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2011 , 29, 041201	1.3	16
155	Role of nonradiative recombination centers and extended defects in nonpolar GaN on light emission efficiency. <i>Applied Physics Letters</i> , 2011 , 98, 072104	3.4	30
154	Comparison of hole traps in n-GaN grown by hydride vapor phase epitaxy, metal organic chemical vapor deposition, and epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 2011 , 109, 123701	2.5	41
153	10 MeV electrons irradiation effects in variously doped n-GaN. <i>Journal of Applied Physics</i> , 2011 , 109, 123703	2.5	22
152	Neutron doping effects in epitaxially laterally overgrown n-GaN. <i>Applied Physics Letters</i> , 2011 , 98, 212107	3.4	8
151	Carrier Removal Rates and Deep Traps in Neutron Irradiated n-GaN Films. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H866	3.9	17
150	GaN as a detector of β particles and neutrons 2011 ,		9
149	Electrical and optical properties of Fe doped AlGaN grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2010 , 107, 023708	2.5	4
148	a-plane GaN hydride vapor phase epitaxy on a-plane GaN templates with and without use of TiN intermediate layers. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2010 , 28, 1039-1043	1.3	1

147	GaN epitaxial films grown by hydride vapor phase epitaxy on polycrystalline chemical vapor deposition diamond substrates using surface nanostructuring with TiN or anodic Al oxide. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010 , 28, 1011-1015	1.3	5
146	Neutron transmutation doping effects in GaN. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010 , 28, 608-612	1.3	26
145	Electrical and luminescent properties and deep traps spectra of N-polar GaN films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010 , 166, 83-88	3.1	9
144	Electrical properties and deep traps spectra of a-plane GaN films grown on r-plane sapphire. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010 , 166, 220-224	3.1	22
143	Shallow and Deep Centers in As-Grown and Annealed MgZnO/ZnO Structures with Quantum Wells. <i>Journal of Electronic Materials</i> , 2010 , 39, 601-607	1.9	4
142	Laterally overgrown GaN/InGaN multi-quantum well heterostructures: Electrical and optical properties. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1383-1385	1.6	1
141	Electrical properties and deep traps spectra of N-polar and Ga-polar AlGaIn films grown by molecular beam epitaxy in a wide composition range. <i>Journal of Applied Physics</i> , 2009 , 105, 113712	2.5	7
140	Electrical properties and deep traps spectra in undoped and Si-doped m-plane GaN films. <i>Journal of Applied Physics</i> , 2009 , 105, 063708	2.5	12
139	Comparison of electrical properties and deep traps in p-Al _x Ga _{1-x} N grown by molecular beam epitaxy and metal organic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2009 , 106, 073706	2.5	13
138	Anisotropy of In incorporation in GaN/InGaN multi-quantum wells prepared by epitaxial lateral overgrowth. <i>Applied Physics Letters</i> , 2009 , 94, 142103	3.4	16
137	Properties of undoped GaN/InGaN multi-quantum-wells and GaN/InGaN p-n junctions prepared by epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 2009 , 105, 123708	2.5	10
136	Alpha particle detection with GaN Schottky diodes. <i>Journal of Applied Physics</i> , 2009 , 106, 103708	2.5	30
135	Electrical properties and deep traps spectra in AlGaIn films with nitrogen and gallium polarities prepared by molecular beam epitaxy. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4870-4872	2.8	5
134	EBIC investigations of defect distribution in ELOG GaN films. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4916-4918	2.8	4
133	Deep centers in bulk AlN and their relation to low-angle dislocation boundaries. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4939-4941	2.8	8
132	EBIC and CL studies of ELOG GaN films. <i>Superlattices and Microstructures</i> , 2009 , 45, 308-313	2.8	14
131	Electrical properties and deep traps spectra in undoped M-plane GaN films prepared by standard MOCVD and by selective lateral overgrowth. <i>Journal of Crystal Growth</i> , 2009 , 311, 2923-2925	1.6	5
130	Persistent photoconductivity in MgZnO alloys. <i>Semiconductors</i> , 2009 , 43, 577-580	0.7	1

129	Nonpolar GaN grown on Si by hydride vapor phase epitaxy using anodized Al nanomask. <i>Applied Physics Letters</i> , 2009 , 94, 022114	3.4	10
128	Annealing effects on electrical properties of MgZnO films grown by pulsed laser deposition. <i>Journal of Applied Physics</i> , 2008 , 103, 083704	2.5	15
127	Electron irradiation of AlGaIn/GaN and AlN/GaN heterojunctions. <i>Applied Physics Letters</i> , 2008 , 93, 152101	3.4	16
126	Electrical and structural properties of AlN/GaN and AlGaIn/GaN heterojunctions. <i>Journal of Applied Physics</i> , 2008 , 104, 053702	2.5	29
125	Improved crystalline quality nonpolar a-GaN films grown by hydride vapor phase epitaxy. <i>Journal of Vacuum Science & Technology B</i> , 2008 , 26, 1937-1941		4
124	Effects of laterally overgrown n-GaN thickness on defect and deep level concentrations. <i>Journal of Vacuum Science & Technology B</i> , 2008 , 26, 990		36
123	Electron Irradiation Effects in GaIn/GaN Multiple Quantum Well Structures. <i>Journal of the Electrochemical Society</i> , 2008 , 155, H31	3.9	12
122	Electrical properties of GaN (Fe) buffers for AlGaIn/GaN high electron mobility transistor structures. <i>Applied Physics Letters</i> , 2008 , 92, 042110	3.4	17
121	Donor nonuniformity in undoped and Si doped n-GaN prepared by epitaxial lateral overgrowth. <i>Applied Physics Letters</i> , 2008 , 92, 042118	3.4	37
120	Deep-level studies in GaN layers grown by epitaxial lateral overgrowth. <i>Thin Solid Films</i> , 2008 , 516, 2035-2040	2.0	12
119	EBIC investigations of GaN layers prepared by epitaxial lateral overgrowth. <i>Journal of Surface Investigation</i> , 2008 , 2, 688-691	0.5	7
118	Electrical properties and deep traps in ZnO films grown by molecular beam epitaxy. <i>Journal of Vacuum Science & Technology B</i> , 2007 , 25, 1794		7
117	Lattice vibrational properties of ZnMgO grown by pulsed laser deposition. <i>Applied Physics Letters</i> , 2007 , 90, 192110	3.4	17
116	Synthesis solute diffusion growth of bulk GaAs: Effects of growth temperature and stoichiometry. <i>Solid-State Electronics</i> , 2007 , 51, 1039-1046	1.7	2
115	Identification of dislocations and their influence on the recombination of charge carriers in gallium nitride. <i>Journal of Surface Investigation</i> , 2007 , 1, 380-385	0.5	5
114	Neutron Radiation Effects in Epitaxially Laterally Overgrown GaN Films. <i>Journal of Electronic Materials</i> , 2007 , 36, 1320-1325	1.9	28
113	Properties of Fe-doped, thick, freestanding GaN crystals grown by hydride vapor phase epitaxy. <i>Journal of Vacuum Science & Technology B</i> , 2007 , 25, 686		21
112	Electrical, photoelectrical, and luminescent properties of doped p-type GaN superlattices. <i>Journal of Vacuum Science & Technology B</i> , 2007 , 25, 69		1

111	Fast neutron irradiation effects in n-GaN. <i>Journal of Vacuum Science & Technology B</i> , 2007 , 25, 436		46
110	Persistent photoconductivity in p-type ZnO(N) grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2007 , 90, 132103	3.4	22
109	Semi-Insulating, Fe-Doped Buffer Layers Grown by Molecular Beam Epitaxy. <i>Journal of the Electrochemical Society</i> , 2007 , 154, H749	3.9	16
108	Studies of Interface States in Sc ₂ O ₃ /GaN, MgO/GaN, and MgScO ₄ /GaN structures. <i>Journal of the Electrochemical Society</i> , 2007 , 154, H115	3.9	16
107	Electrical Properties of ZnO(P) and ZnMgO(P) Films Grown by Pulsed Laser Deposition. <i>Journal of the Electrochemical Society</i> , 2007 , 154, H825	3.9	10
106	Deep traps responsible for hysteresis in capacitance-voltage characteristics of AlGaIn/GaN heterostructure transistors. <i>Applied Physics Letters</i> , 2007 , 91, 232116	3.4	43
105	Spatial variations of doping and lifetime in epitaxial laterally overgrown GaN. <i>Applied Physics Letters</i> , 2007 , 90, 152114	3.4	42
104	Neutron irradiation effects in AlGaIn/GaN heterojunctions. <i>Physica B: Condensed Matter</i> , 2006 , 376-377, 523-526	2.8	17
103	Electrical properties of undoped bulk ZnO substrates. <i>Journal of Electronic Materials</i> , 2006 , 35, 663-669	1.9	37
102	Microcathodoluminescence and electrical properties of GaN epitaxial layers grown on thick freestanding GaN substrates. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 790		2
101	Neutron irradiation effects in undoped n-AlGaIn. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 1094		11
100	Neutron irradiation effects in p-GaN. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 2256		28
99	Optical properties of GaAs _{1-x} N _x alloys grown by molecular beam epitaxy. <i>Philosophical Magazine</i> , 2006 , 86, 3477-3486	1.6	4
98	Electrical Properties, Deep Levels Spectra and Luminescence of Undoped GaN/InGaIn Multi-quantum-well Structures as Affected by Electron Irradiation. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 955, 1		
97	Defects in Electron and Neutron Irradiated n-GaN: Disordered Regions Versus Point Defects. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 955, 1		3
96	Electrical and optical properties of doped p-type GaN superlattices. <i>Applied Physics Letters</i> , 2006 , 89, 112127	3.4	2
95	Fermi level pinning in heavily neutron-irradiated GaN. <i>Journal of Applied Physics</i> , 2006 , 100, 093715	2.5	34
94	Residual impurities and native defects in 6H-SiC bulk crystals grown by halide chemical-vapor deposition. <i>Journal of Applied Physics</i> , 2006 , 99, 013508	2.5	19

93	Electrical and recombination properties and deep traps spectra in MOCVD ELOG GaN layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 2087-2090		19
92	Properties and annealing stability of Fe doped semi-insulating GaN structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2476-2479		11
91	Changes induced in electrical properties and deep level spectra of p-AlGaIn films by treatment in hydrogen plasma and by proton implantation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2480-2483		1
90	Electrical and optical properties of p-GaN films implanted with transition metal impurities. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2520-2524		1
89	Electrical and optical properties of GaCrN films grown by molecular beam epitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005 , 23, 1		9
88	Neutron irradiation effects on electrical properties and deep-level spectra in undoped n-AlGaIn/GaN heterostructures. <i>Journal of Applied Physics</i> , 2005 , 98, 033529	2.5	43
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